# BLC9G20LS-470AVT

# Power LDMOS transistor Rev. 3 — 24 November 2017

**AMMPLEON** 

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

470 W LDMOS packaged asymmetric Doherty power transistor for base station applications at frequencies from 1805 MHz to 1990 MHz.

#### Typical performance

Typical RF performance at  $T_{case} = 25$  °C in an asymmetrical Doherty production test circuit.  $V_{DS}$  = 28 V;  $I_{Dq}$  = 500 mA (main);  $V_{GS(amp)peak}$  = 0.5 V, unless otherwise specified.

Test signal	f	V <sub>DS</sub>	P <sub>L(AV)</sub>	G <sub>p</sub>	η <sub>D</sub>	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	1805 to 1880	28	80	16	49	-35 <u>[1]</u>

<sup>[1]</sup> Test signal: 3GPP test model 1; 64 DPCH; PAR = 7.2 dB at 0.01% probability on CCDF per carrier.

#### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Designed for broadband operation (1805 MHz to 1990 MHz)
- Asymmetric design to achieve optimum efficiency across the band
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

#### 1.3 Applications

 RF power amplifiers for base stations and multi carrier applications in the 1805 MHz to 1990 MHz frequency range

### 2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
1	drain2 (peak)			0.7
2	drain1 (main)		7 2 1 6	2, 7
3	gate1 (main)		5	
4	gate2 (peak)		3 4	3——5
5	source	[1]		4—
6	video decoupling (peak)			' <b>⊢</b> ¬
7	video decoupling (main)			1, 6 aaa-014884

<sup>[1]</sup> Connected to flange.

### 3. Ordering information

Table 3. Ordering information

Type number	Packag	ackage					
	Name	Description	Version				
BLC9G20LS-470AVT	-	air cavity plastic earless flanged package; 6 leads	SOT1258-1				

### 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage		-	65	V
V <sub>GS(amp)main</sub>	main amplifier gate-source voltage		-5	+13	V
V <sub>GS(amp)peak</sub>	peak amplifier gate-source voltage		<b>-5</b>	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	<u>[1]</u>	-	225	°C

Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>		$V_{DS}$ = 28 V; $I_{Dq}$ = 400 mA (main); $V_{GS(amp)peak}$ = 0.5 V; $T_{case}$ = 80 °C		
		$P_L = 49 \text{ dBm}$	0.26	K/W
		$P_L = 51 \text{ dBm}$	0.20	K/W

#### 6. Characteristics

Table 6. DC characteristics

 $T_i$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	rice				1	
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.44 \text{ mA}$	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 144 mA	1.5	2	2.5	V
$V_{GSq}$	gate-source quiescent voltage	V <sub>DS</sub> = 30 V; I <sub>D</sub> = 864 mA	1.8	2.1	2.35	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 32 V	-	-	2.8	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	31.5	-	Α
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	280	nA
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 5.04 A	-	10.2	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 5.04 \text{ A}$	-	99	165	mΩ
Peak dev	rice					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.6 \text{ mA}$	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 260 mA	1.5	2	2.5	V
$V_{GSq}$	gate-source quiescent voltage	V <sub>DS</sub> = 30 V; I <sub>D</sub> = 1560 mA	1.4	1.85	2.25	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 32 V	-	-	2.8	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	49	-	Α
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	280	nA
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 9.1 A	-	17.3	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 9.1 \text{ A}$	-	51	85	mΩ

#### Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 400 mA (main);  $V_{GS(amp)peak}$  = 0.5 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 1805 MHz to 1880 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$G_p$	power gain	P <sub>L(AV)</sub> = 80 W	14.5	15.7	-	dB
RLin	input return loss	P <sub>L(AV)</sub> = 80 W	-	-10	-6	dB
$\eta_{D}$	drain efficiency	P <sub>L(AV)</sub> = 80 W	42.5	47.5	-	%
ACPR	adjacent channel power ratio	P <sub>L(AV)</sub> = 80 W	-	-33	-28	dBc

#### Table 8. RF characteristics

Test signal: pulsed CW;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 400 mA (main);  $V_{GS(amp)peak}$  = 0.5 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 1805 MHz to 1880 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P <sub>L(M)</sub>	peak output power		380	425	-	W

### 7. Test information

#### 7.1 Ruggedness in Doherty operation

The BLC9G20LS-470AVT is capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 28 V;  $I_{Dq}$  = 400 mA (main);  $V_{GS(amp)peak}$  = 0.5 V;  $P_L$  = 250 W (CW); f = 1805 MHz.

### 7.2 Impedance information

**Table 9. Typical impedance of main device** Measured load-pull data of main device;  $I_{Dq} = 400 \text{ mA (main)}$ ;  $V_{DS} = 28 \text{ V}$ .

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]					
(MHz)	<b>(</b> Ω <b>)</b>	(Ω)	(W)	(%)	(dB)					
Maximum po	Maximum power load									
1805	1.03 – j4.87	1.22 – j3.6	206.0	60.0	15.16					
1843	2.10 - j4.50	1.22 – j3.6	200.0	60.0	14.93					
1880	1.58 – j5.07	1.22 – j3.6	200.4	60.3	15.34					
Maximum dr	ain efficiency load				•					
1805	1.03 – j4.87	2.31 – j2.74	142.5	68.12	17.44					
1843	2.10 - j4.50	2.08 – j2.55	137.0	68.24	17.06					
1880	1.58 – j5.07	1.90 – j2.76	146.0	67.8	17.30					

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

**Table 10.** Typical impedance of peak device Measured load-pull data of peak device;  $I_{Dq} = 1300 \text{ mA}$  (peak);  $V_{DS} = 28 \text{ V}$ .

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]					
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)					
Maximum	Maximum power load									
1805	1.06 – j5.55	2.0 - j3.8	322.8	56.90	15.60					
1843	1.89 – j5.55	2.0 - j3.8	315.5	56.18	15.16					
1880	1.86 – j6.21	2.2 – j4.1	313.3	55.30	15.74					
Maximum o	drain efficiency loa	d			·					
1805	1.06 – j5.55	2.76 - j2.70	267.9	64.5	17.23					
1843	1.89 – j5.55	2.68 - j2.24	234.4	63.5	17.04					
1880	1.86 – j6.21	2.68 - j2.24	230.7	63.5	17.79					

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

<sup>[2]</sup> at 3 dB gain compression.

<sup>[2]</sup> at 3 dB gain compression.

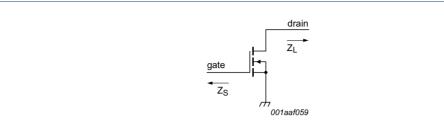


Fig 1. Definition of transistor impedance

### 7.3 Recommended impedances for Doherty design

Table 11. Typical impedance of main device at 1 : 1 load Measured load-pull data of main device;  $I_{Dq}$  = 400 mA (main);  $V_{DS}$  = 28 V.

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [3]	G <sub>p</sub> [3]
(MHz)	(Ω)	<b>(</b> Ω <b>)</b>	(dBm)	(%)	(dB)
1805	1.03 – j4.87	1.83 – j3.50	52.6	46.5	19.1
1843	2.10 - j4.50	1.67 – j3.30	52.7	47.0	19.2
1880	1.58 – j5.07	1.50 – j3.12	52.8	48.1	19.4

- [1] Z<sub>S</sub> and Z<sub>L</sub> defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at  $P_{L(AV)} = 49 \text{ dBm}$ .

Table 12. Typical impedance of main device at 1: 2.5 load

Measured load-pull data of main device;  $I_{Dq}$  = 400 mA (main);  $V_{DS}$  = 28 V.

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [3]	G <sub>p</sub> [3]
(MHz)	<b>(</b> Ω <b>)</b>	<b>(</b> Ω <b>)</b>	(dBm)	(%)	(dB)
1805	1.03 – j4.87	2.56 - j1.80	50.48	63.6	21.2
1843	2.10 - j4.50	2.84 - j1.96	50.46	64.0	21.4
1880	1.58 – j5.07	3.14 – j2.12	50.40	64.0	21.5

- [1]  $Z_S$  and  $Z_L$  defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at  $P_{L(AV)} = 49 \text{ dBm}$ .

#### 7.4 Test circuit

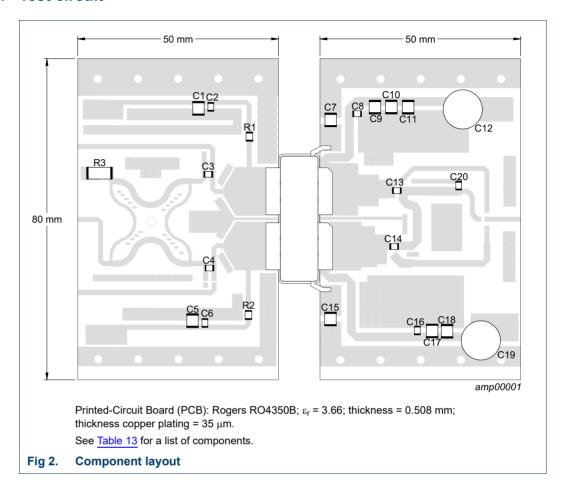


Table 13. List of components

See Figure 2 for component layout.

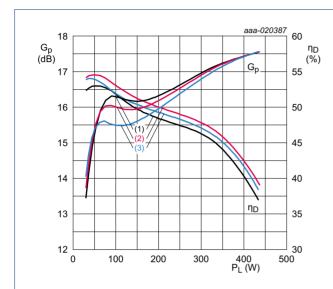
Component	Description	Value	Remarks
C1, C5, C7, C9, C10, C11, C15, C17, C18	multilayer ceramic chip capacitor	10 μF, 50 V	1
C2, C3, C4, C6, C8, C16	multilayer ceramic chip capacitor	36 pF	1
C12, C19	electrolytic capacitor	1000 μF, 63 V	
C13	multilayer ceramic chip capacitor	10 pF	1
C14	multilayer ceramic chip capacitor	27 pF	1
C20	multilayer ceramic chip capacitor	0.1 pF	1
R1, R2	resistor	5.1 Ω	SMD 0805
R3	resistor	50 Ω	SMD 0805

<sup>[1]</sup> Murata or capacitor of same quality

[2] American Technical Ceramics type 600F or capacitor of same quality

#### 7.5 Graphical data

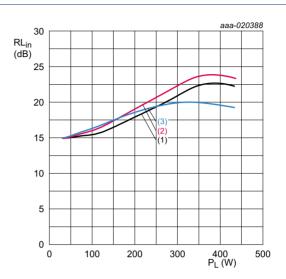
#### 7.5.1 Pulsed CW



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 400 mA (main device);  $V_{GS(amp)peak}$  = 0.5 V.

- (1) f = 1805 MHz
- (2) f = 1842.5 MHz
- (3) f = 1880 MHz

Fig 3. Power gain and drain efficiency as function of output power; typical values

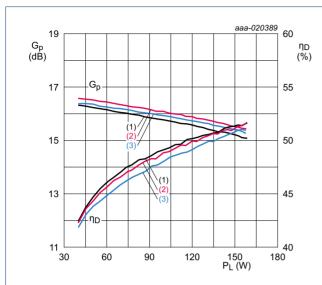


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 400 mA (main device);  $V_{GS(amp)peak}$  = 0.5 V.

- (1) f = 1805 MHz
- (2) f = 1842.5 MHz
- (3) f = 1880 MHz

Fig 4. Input return loss as a function of output power; typical values

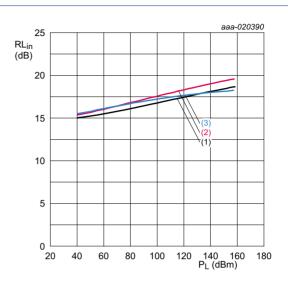
#### 7.5.2 1-Carrier W-CDMA



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 400 mA (main device);  $V_{GS(amp)peak}$  = 0.5 V.

- (1) f = 1805 MHz
- (2) f = 1842.5 MHz
- (3) f = 1880 MHz

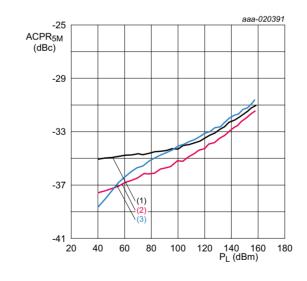
Fig 5. Power gain and drain efficiency as function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 400 mA (main device);  $V_{GS(amp)peak}$  = 0.5 V.

- (1) f = 1805 MHz
- (2) f = 1842.5 MHz
- (3) f = 1880 MHz

Fig 6. Input return loss as a function of output power; typical values

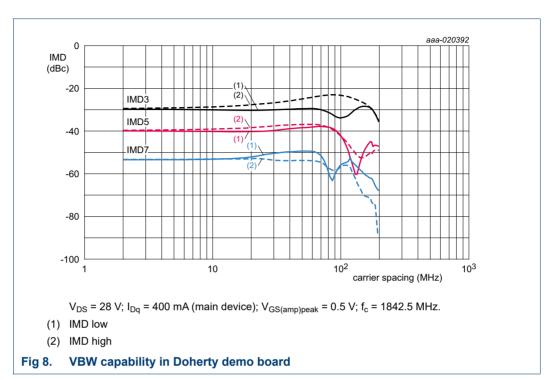


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 400 mA (main device);  $V_{GS(amp)peak}$  = 0.5 V.

- (1) f = 1805 MHz
- (2) f = 1842.5 MHz
- (3) f = 1880 MHz

Fig 7. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

#### 7.5.3 2-Tone VBW



### 8. Package outline

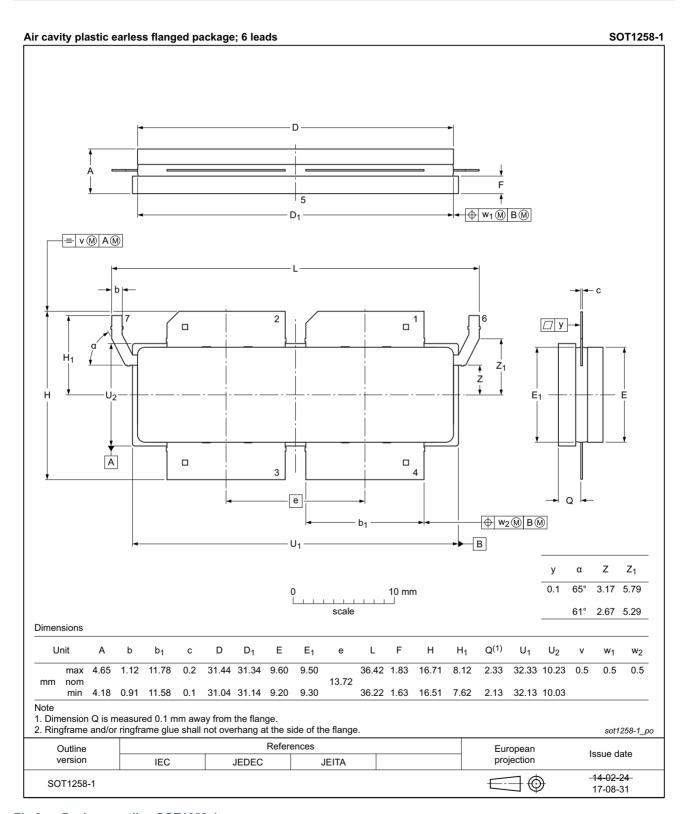


Fig 9. Package outline SOT1258-1

### 9. Handling information

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 14. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

#### 10. Abbreviations

Table 15. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VBW	Video BandWidth
W-CDMA	Wideband Code Division Multiple Access

### 11. Revision history

Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC9G20LS-470AVT v.3	20171124	Product data sheet	-	BLC9G20LS-470AVT v.2
Modifications:	<u>Table 2 on page 2</u> : changed simplified version drawing SOT1258-3 to SOT1258-1			
	Table 3 on pa	ige 2: changed version SOT1	258-3 to SOT1258-1	
	• Figure 2 on p	age 6: updated figure		
	• Figure 9 on p	age 10: changed package ou	tline drawing SOT12	58-3 to SOT1258-1
BLC9G20LS-470AVT v.2	20161202	Product data sheet	-	BLC9G20LS-470AVT v.1
BLC9G20LS-470AVT v.1	20160224	Product data sheet	-	-

BLC9G20LS-470AVT

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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## **AMPLEON**

# **BLC9G20LS-470AVT**

#### **Power LDMOS transistor**

### 14. Contents

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.